

SANYO	No. 1853A	2SA1434
		PNP Epitaxial Planar Silicon Transistor High h_{FE} , Low-Frequency General-Purpose Amp Applications

Applications

- Low frequency general-purpose amplifiers, drivers, muting circuits

Features

- Very small-sized package permitting 2SA1434-used sets to be made smaller, slimmer.
- Adoption of FBET process
- High DC current gain ($h_{FE}=500$ to 1200)
- Low collector-to-emitter saturation voltage ($V_{CE(sat)} \leq 0.5V$)
- High V_{EBO} ($V_{EBO} \geq 15V$)

Absolute Maximum Ratings at $T_a=25^\circ C$

			unit
Collector to Base Voltage	V_{CB0}	-60	V
Collector to Emitter Voltage	V_{CE0}	-50	V
Emitter to Base Voltage	V_{EBO}	-15	V
Collector Current	I_C	-100	mA
Collector Current(Pulse)	I_{CP}	-200	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature	T_{stg}	-55 to 125	$^\circ C$

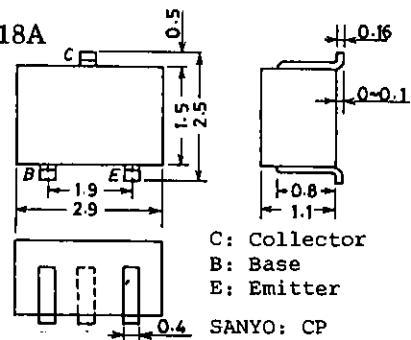
Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-10V, I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-5V, I_C=-10mA$	500	800	1200	
Gain-Bandwidth Product	f_T	$V_{CE}=-10V, I_C=-10mA$		100		MHz
Output Capacitance	c_{ob}	$V_{CB}=-10V, f=1MHz$		4.8		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-50mA, I_B=-1mA$	-0.2	-0.5		V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-50mA, I_B=-1mA$	-0.8	-1.1		V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-60			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, R_{BE}=\infty$	-50			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-15			V

Marking :FL

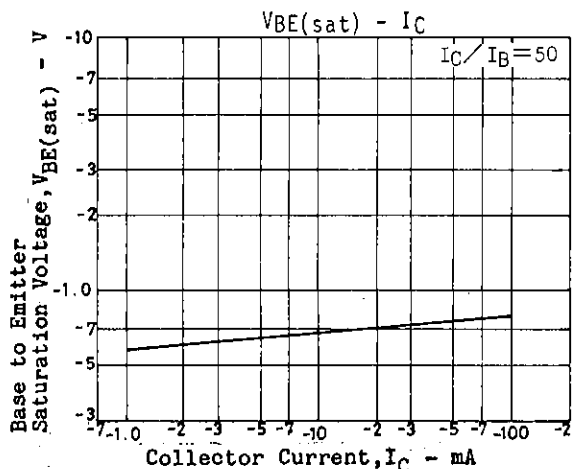
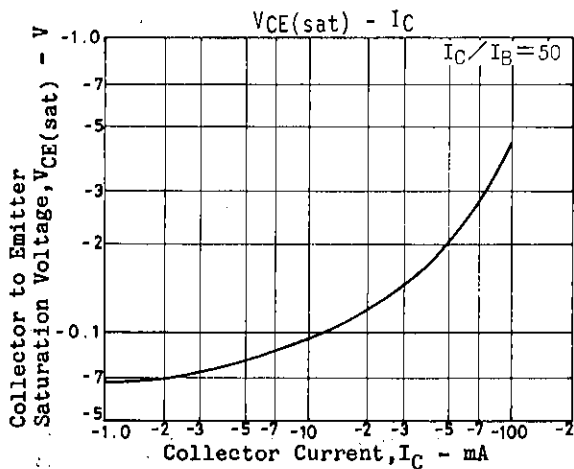
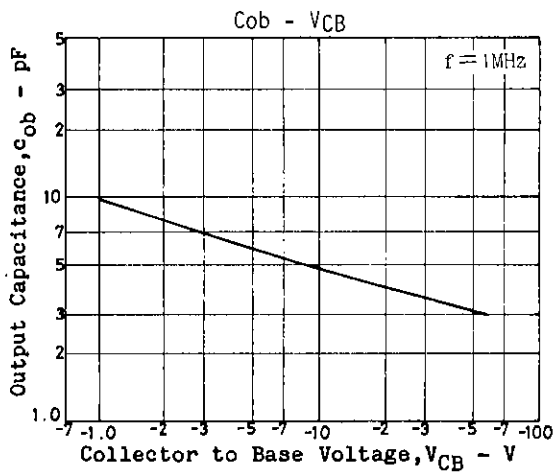
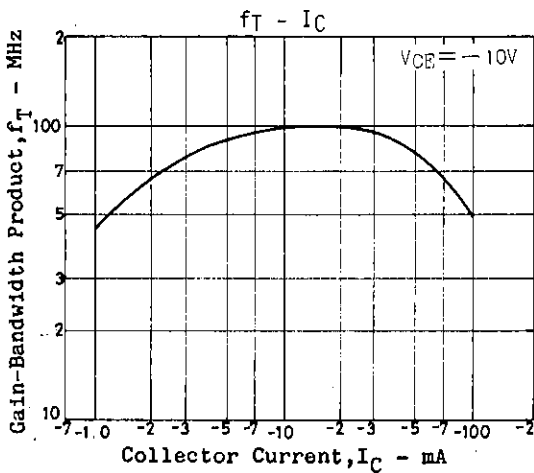
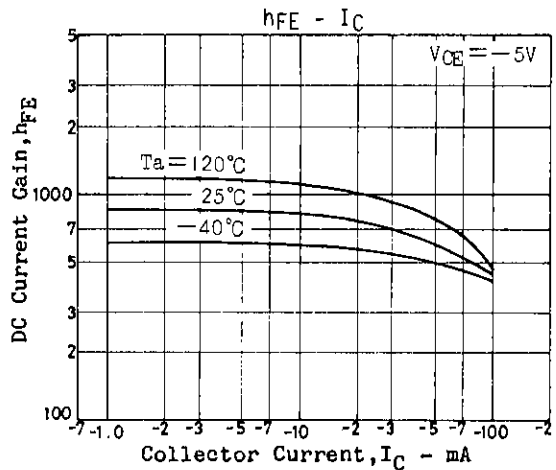
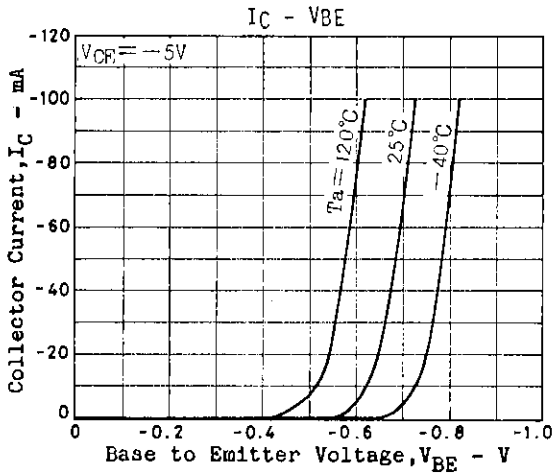
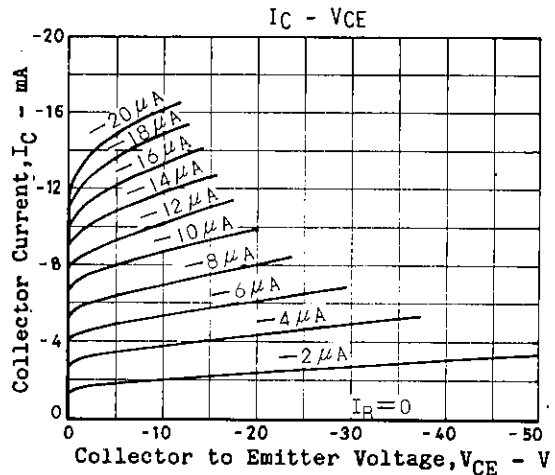
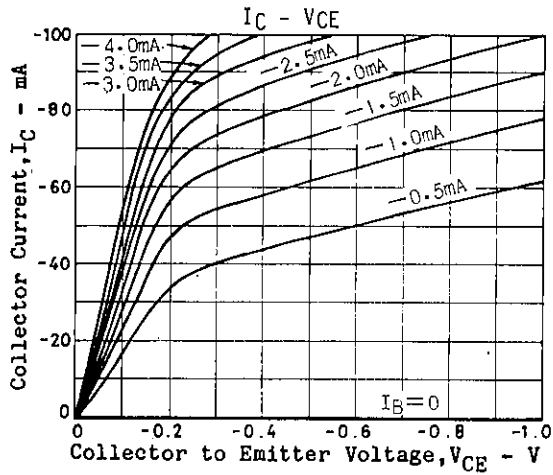
Package Dimensions 2018A

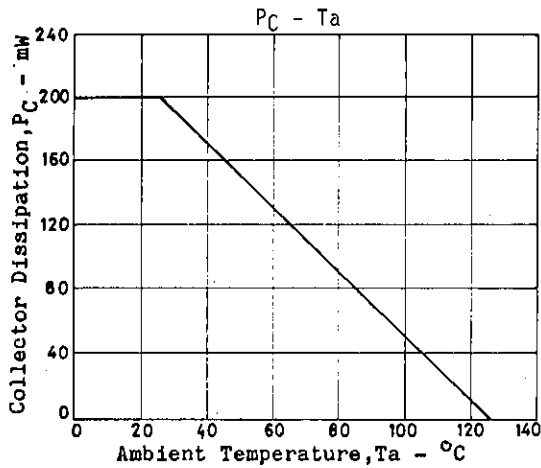
(unit:mm)



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